



DMN2028UVT

Product Summary

V _{(BR)DSS}	RDS(ON) Max	Ι _D Τ _A = +25°C
20V	$24m\Omega @ V_{GS} = 4.5V$	6.2A
200	$32m\Omega @ V_{GS} = 2.5V$	0.2A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Backlighting

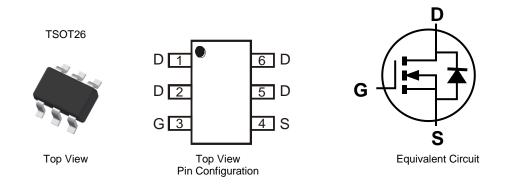
N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (£3)
- Weight: 0.013 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2028UVT-7	TSOT26	3,000/Tape & Reel
DMN2028UVT-13	TSOT26	10,000/Tape & Reel

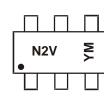
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \mathsf{N2V}=\mathsf{Product}\ \mathsf{Type}\ \mathsf{Marking}\ \mathsf{Code}\\ \mathsf{YM}=\mathsf{Date}\ \mathsf{Code}\ \mathsf{Marking}\\ \mathsf{Y}=\mathsf{Year}\ (ex:\ \mathsf{C}=2015)\\ \mathsf{M}=\mathsf{Month}\ (ex:\ 9=\mathsf{September}) \end{array}$

Date Code Key

Notes:

Year	201	4	2015		2016	20	17	2018		2019	2	020
Code	В		С		D	I		F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
WOITUI	oun	1.00	iviai		inay	oun	Juli	Aug	0cp	001	1101	000



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	ID	6.2	A		
Maximum Body Diode Forward Current (Note 6)		Is	1.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	40	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.2	W	
Thermal Desistance, lunction to Archievet (Note 5)	Steady state		105	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}JA}$	76	C/VV	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.6	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	5	76	°C/W	
memai Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	50		
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	15		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	T. m	Max	Unit	Test Condition
	Symbol	WIIN	Тур	wax	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				1	1	1
Drain-Source Breakdown Voltage	BV _{DSS}	20			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	IDSS			1	μA	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.4		1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	20	24	mΩ	$V_{GS} = 4.5V, I_D = 6.2A$
	R _{DS(ON)}	_	24	32	11152	$V_{GS} = 2.5V, I_D = 5.2A$
Diode Forward Voltage	V _{SD}			1.2	V	$V_{GS} = 0V, I_{S} = 1.3A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		856	_		
Output Capacitance	Coss	_	83		pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	78			T = T.000172
Total Gate Charge	Qg	_	8.3	_		
Gate-Source Charge	Q _{gs}	_	1.3		nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.2A$
Gate-Drain Charge	Q _{gd}		3.1	_		
Turn-On Delay Time	t _{D(ON)}	_	13.2			
Turn-On Rise Time	t _R	_	12.6			$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	65		ns	$I_D = 1A, R_G = 6\Omega$
Turn-Off Fall Time	tF	_	22			

Notes:

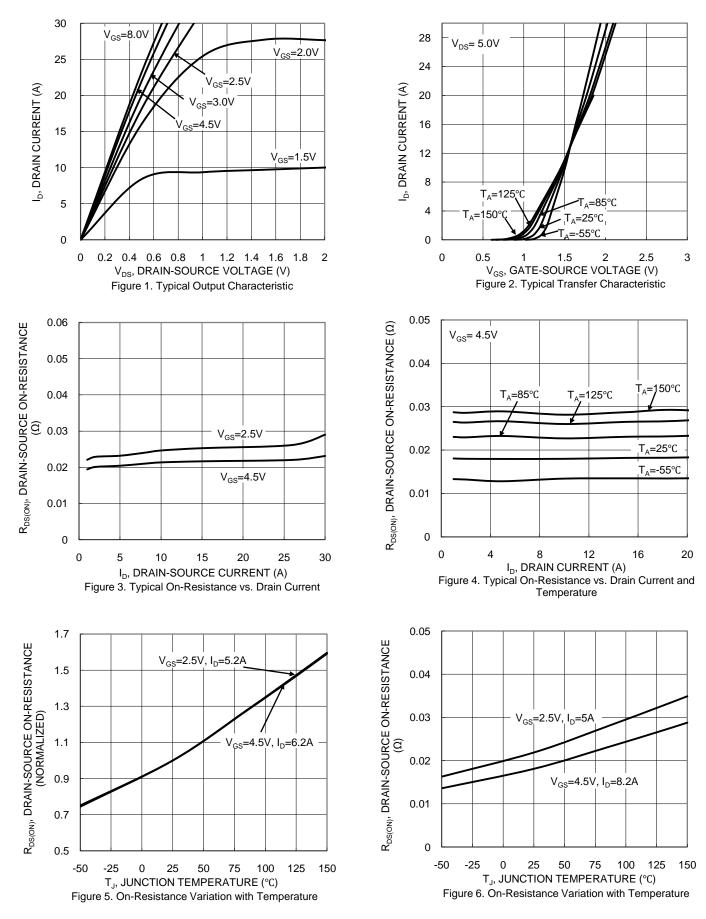
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.



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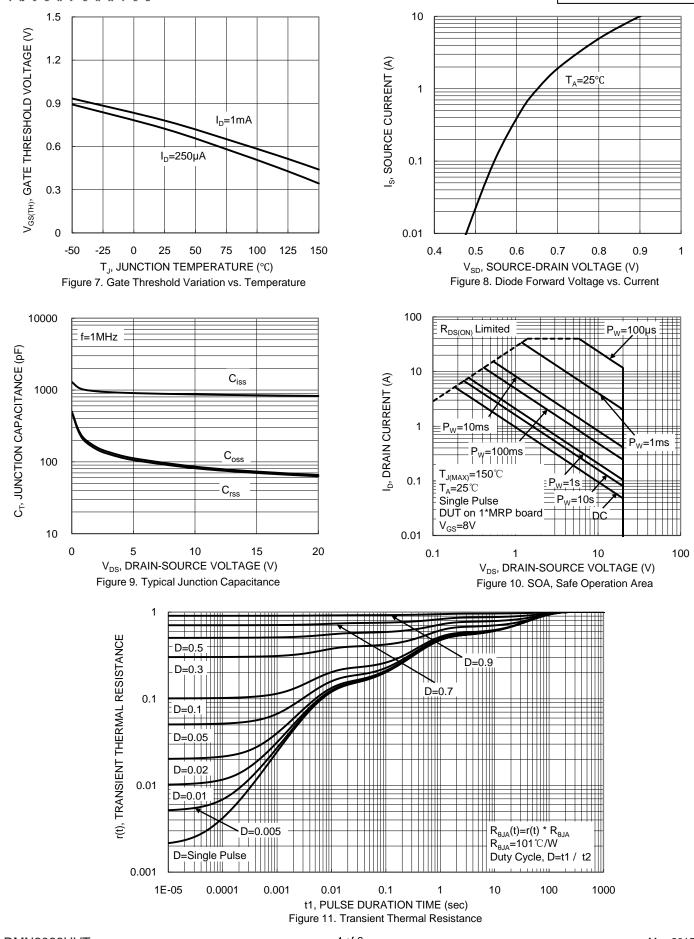


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NEW PRODUCT

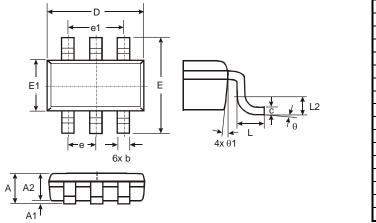
DMN2028UVT





Package Outline Dimensions

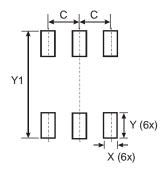
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



A — 1.00 — A1 0.01 0.10 — A2 0.84 0.90 — D — — 2.90 E — — 2.80 E1 — — 1.60 b 0.30 0.45 — c 0.12 0.20 — e — — 0.95 e1 — — 1.90 L 0.30 0.50 —	TSOT26						
A1 0.01 0.10 — A2 0.84 0.90 — D — — 2.90 E — — 2.80 E1 — — 1.60 b 0.30 0.45 — c 0.12 0.20 — e — — 0.95 e1 — — 1.90 L 0.30 0.50 —	Dim	Min	Max	Тур			
A2 0.84 0.90 — D — — 2.90 E — — 2.80 E1 — — 1.60 b 0.30 0.45 — c 0.12 0.20 — e — — 0.95 e1 — — 1.90 L 0.30 0.50 —	Α		1.00				
D 2.90 E 2.80 E1 1.60 b 0.30 0.45 c 0.12 0.20 e 0.95 e1 1.90 L 0.30 0.50	A1	0.01	0.10				
E 2.80 E1 1.60 b 0.30 0.45 c 0.12 0.20 e 0.95 e1 1.90 L 0.30 0.50	A2	0.84	0.90	-			
E1 — — 1.60 b 0.30 0.45 — c 0.12 0.20 — e — — 0.95 e1 — — 1.90 L 0.30 0.50 —	D			2.90			
b 0.30 0.45 c 0.12 0.20 e 0.95 e1 1.90 L 0.30 0.50	Ε		-	2.80			
c 0.12 0.20 e 0.95 e1 1.90 L 0.30 0.50	E1			1.60			
e — — 0.95 e1 — — 1.90 L 0.30 0.50 —	b	0.30	0.45				
e1 — — 1.90 L 0.30 0.50 —	С	0.12	0.20				
L 0.30 0.50 —	е			0.95			
	e1			1.90			
L2 — — 0.25	L	0.30	0.50	-			
	L2		-	0.25			
θ 0° 8° 4°	θ	0°	8°	4°			
θ1 4° 12° —	θ1	4°	12°				
All Dimensions in mm	All D	imens	ions ir	n mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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